

REMARKS

Reconsideration of the present application is respectfully requested. Claims 1-7 now stand rejected as anticipated under 35 U.S.C. §102 by Wang et al. U.S. Patent No. 6,448,167, and claims 8 and 15 stand rejected as unpatentable over Wang in view of Kepler.

The applicants do not agree that claim 1 is not patentable in view of Wang et al. The applicants observe that Wang et al. does not disclose or suggest a procedure in which the oxide layer is selectively removed from the surface of the device, leaving oxide film 112 in the non-silicide transistor region 200, as shown in Fig. 3C. The specification of the present application, at page 10, indicates that:

Then, a resist is deposited over the oxide film 112, and then, is patterned into a predetermined pattern by photolithography and etching. Then, the oxide film 112 is wet-etched through the use of hydrofluoric acid etchant with the patterned resist being used as a mask such that the oxide film 112 remains only in the non-silicide transistor region 200, as illustrated in FIG. 3C.

In contrast, Wang et al. appears to teach a non-selective removal of the oxide film. See FIGS. 8 and 9 of Wang.

Claim 1 has been amended to claim the invention as regarded by the applicants with more particularity, and is believed to be patentable over Wang et al.

Claims 16-21 are added in this paper and are believed to be patentable over Wang et al. for the above stated reasons. Furthermore, the new claims recite that thermal annealing for activation of impurity ions takes place after oxide film formation; not immediately after implantation of impurity ions. This is intended to prevent a recess of the shoulder of a shallow trench isolation film from deepening, in order to prevent leakage. See specification at page 8 lines 1-11.

Wherefore, based upon the foregoing, it is respectfully submitted that the present application is in condition of allowance and a relatively early reply is requested.

Respectfully submitted,

A handwritten signature in black ink, consisting of a large, stylized 'R' followed by a series of loops and a final horizontal stroke.

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